

Contents

1	Introduction	1
1.1	Introduction	1
1.2	Optical Phenomena in Semiconductors	2
1.3	Band Structure and Fundamental Bandgap	5
1.4	Quasi Particles in Solids	7
1.4.1	Electrons and Holes	7
1.4.2	Excitons	9
1.4.3	Phonons	10
1.4.4	Plasmons	12
1.5	Extrinsic Factors Affecting the Bandgap: Temperature and Stress	12
1.5.1	Temperature	12
1.5.2	Stress	13
1.6	Low Dimension Structures	14
1.6.1	Quantum Confinement	14
1.6.2	The Density of States in Quantum Confined Structures	17
1.7	Extrinsic Semiconductors. Energy Levels Inside the Forbidden Bandgap	18
1.7.1	Point Defects	18
1.7.2	Extended Defects	20
1.8	Doped Semiconductors: Effects on the Band Gap	21
1.9	Interaction of the Semiconductor with Electromagnetic Waves	24
1.9.1	Macroscopic Approach. Optical Constants	24
1.10	The Oscillator Model for the Optical Constants	26
1.10.1	Dielectric Function	26
1.10.2	Kramers Kronig Relations	27
1.11	Optical Reflection	28

1.12	Optical Transitions. Light Absorption and Emission	28
1.12.1	Einstein Coefficients.	29
1.12.2	Microscopic Description of the Optical Absorption in Semiconductors	31
1.12.3	Microscopic Description of the Stimulated Emission in Semiconductors	34
1.12.4	Microscopic Description of the Spontaneous Emission in Semiconductors	35
1.12.5	Indirect Optical Transitions	36
1.12.6	The Influence of Disorder and Doping in the Absorption Coefficient. Urbach Tail	37
1.12.7	Defect and Impurity Absorption.	38
1.12.8	Excitonic Absorption	38
1.13	Carrier Recombination. Luminescence	40
1.13.1	Non-radiative Recombination	41
1.13.2	Luminescence	41
1.13.3	Diffusion Length	44
1.13.4	Surface Recombination.	45
1.13.5	Exciton Recombination.	45
	References	46
2	Basics of Optical Spectroscopy: Transmission and Reflection Measurements, Their Analysis, and Related Techniques	49
2.1	Introduction	49
2.2	Samples and Spectroscopic Equipment	52
2.2.1	Samples	52
2.2.2	Spectrophotometer	54
2.2.3	Fourier-Transform Spectrometer.	57
2.3	Extraction of the Optical Constants from Standard Measurements	59
2.4	The Link Between the Optical Constants and Material Properties	61
2.4.1	Absorption Spectra and Bandstructure	61
2.4.2	Absorption Spectra and Extrinsic Absorption.	63
2.4.3	Absorption Spectra Obtained by Using Polarized Light	64
2.4.4	Reflection Spectra	65
2.4.5	Modulation Spectroscopy and Photoreflexion	67
2.5	Related Techniques	69
2.5.1	Photoacoustic Spectroscopy.	69
2.5.2	Ellipsometry	70
2.5.3	Mapping.	71
	References	75

3	Raman Spectroscopy	77
3.1	Introduction	77
3.2	The Light Scattering by Phonons	80
3.2.1	Wavevector and Energy Selection Rules	80
3.2.2	Symmetry Selection Rules	81
3.3	What Semiconductor Properties Can Be Investigated with Raman Spectroscopy?	84
3.4	Experimental Description	85
3.4.1	Raman Spectrometer	85
3.4.2	The Detectors	88
3.4.3	Laser Sources	89
3.4.4	Raman Imaging	91
3.4.5	The Lateral Resolution	95
3.4.6	Probe Depth	99
3.4.7	The Microscope Objectives	103
3.5	Case Applications	106
3.5.1	Stress in Si Microelectronic Devices	106
3.5.2	Doping	114
3.5.3	Temperature Measurements Using μ -R Spectroscopy . . .	125
3.5.4	Size Effects. Phonon Confinement	132
	References	136
4	Photoluminescence (PL) Techniques	143
4.1	Introduction	143
4.2	Probed Sample Region	145
4.2.1	Vertical Spatial Resolution—The 'Information Depth'	145
4.2.2	Lateral Spatial Resolution	149
4.2.3	The Impact of Actual Spatial Carrier Distributions to the PL-Line Shape	150
4.3	PL Setups and Methodology	150
4.3.1	Standard cw PL Setup	150
4.3.2	Resonantly Excited PL	156
4.3.3	PL Excitation Spectroscopy	157
4.4	Mechanisms Contributing to the PL Spectrum	159
4.4.1	Introduction	159
4.4.2	Band-to-Band Transitions	161
4.4.3	Free Excitons	161
4.4.4	Band-to-Band Transitions Versus Excitonic Transitions	163
4.4.5	Bound Excitons	164
4.4.6	Defect Related Transitions	165
4.4.7	PL Contributions at Energies Larger Than E_g	167
4.4.8	The Impact of the Parameter Excitation Density	169

4.5	Applications of Steady-State Photoluminescence	171
4.5.1	Analysis of E_g Shifts	171
4.5.2	Surface Recombination Velocity	175
4.5.3	Rare Earth or Transition Metal Atoms in Semiconductors	176
4.5.4	Infrared Fourier-Transform Photoluminescence	179
4.5.5	Photoluminescence from Indirect Materials	180
4.6	Time-Resolved Photoluminescence (TR PL)	182
4.6.1	Introduction	182
4.6.2	TR PL: Experimental	184
4.6.3	TR PL: Practical Examples	187
4.6.4	Ultrafast TR PL	190
4.7	Photoluminescence Mapping	192
4.7.1	PL Mapping: Experimental	192
4.7.2	PL Mapping: Practical Examples	194
4.7.3	Ring-Shaped PL Pattern in Biased Quantum Wells.	198
4.7.4	Near-Field Scanning Optical Microscope Based PL	200
4.8	Photoluminescence at Devices	202
4.8.1	Introduction	202
4.8.2	Strain Analysis in Devices by Means of PL Scanning	203
4.8.3	Temperature Measurements at Operating Devices.	204
4.8.4	TR PL at Devices	204
4.8.5	PL Mapping at Opened Devices	206
	References	208
5	Cathodoluminescence	213
5.1	Introduction	213
5.2	e-Beam Excitation. The Generation Function.	216
5.2.1	Excitation with an e-Beam	216
5.2.2	The Generation Function	217
5.3	Monte Carlo Simulation	223
5.4	Charge Effects. The Dead Layer	226
5.5	The CL Signal.	229
5.6	Experimental Set-Up	235
5.7	Electrostatic Charge	240
5.8	Case Applications	241
5.8.1	Carrier Diffusion Length.	241
5.8.2	In-Depth Analysis: Multilayer Structures. Laser Diodes and AlGaIn/GaN HEMTS	244
5.8.3	Low Electron Energy Cathodoluminescence	249
5.8.4	Spectral Images: Orientation Patterned GaAs Crystals	252
5.8.5	Dislocations in Si-Doped GaAs	255
5.8.6	Nanostructures.	257

5.9	PL and CL: A Comparative	259
	References	259
6	Photoelectrical Spectroscopy	265
6.1	Introduction	265
6.2	Generation of Photocurrents	268
6.2.1	Conductivity and Photoconductivity	268
6.2.2	Intrinsic Photocurrent Spectra $I_{PC}(\hbar\omega)$	270
6.2.3	Intrinsic PC Spectra in Presence of Surface Recombination	273
6.2.4	Photoconductivity from QWs, Quantum Dots, and Excitonic Photoconductivity	275
6.2.5	Extrinsic Photoconductivity	277
6.2.6	Other Photoelectrical Effects	281
6.3	Experimental.	283
6.3.1	Photocurrent Setups	283
6.3.2	Sample Geometry	286
6.3.3	Direct and Time-Dependent PCs	288
6.3.4	Transient Photocurrent Spectroscopy	291
6.4	Selected Applications of Photocurrent Spectroscopy for Analytical Purposes	292
6.4.1	Intrinsic Interband PC	292
6.4.2	Defect-Related (Extrinsic) Photoconductivity	294
6.4.3	Laser Beam Induced Current (LBIC)	295
	References	299
	Index	301